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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/809,011	03/25/2004	Eiji Nishibe	10417-103002 7829	
26211 7	590 03/23/2006		EXAMINER	
FISH & RICHARDSON P.C.			LINDSAY JR, WALTER LEE	
P.O. BOX 1022 MINNEAPOLIS, MN 55440-1022			ART UNIT	PAPER NUMBER
			2812	

DATE MAILED: 03/23/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
Office Action Summan	10/809,011	NISHIBE ET AL.				
Office Action Summary	Examiner	Art Unit				
	Walter L. Lindsay, Jr.	2812				
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address				
A SHORTENED STATUTORY PERIOD FOR REPLY WHICHEVER IS LONGER, FROM THE MAILING DA  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory period w  - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	ATE OF THIS COMMUNICATION  16(a). In no event, however, may a reply be tim  iill apply and will expire SIX (6) MONTHS from to cause the application to become ABANDONED	l. ely filed the mailing date of this communication. D (35 U.S.C. § 133).				
Status						
1) Responsive to communication(s) filed on						
,	action is non-final.					
,—						
	closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims	•					
4) Claim(s) <u>5-8</u> is/are pending in the application.						
4a) Of the above claim(s) is/are withdrawn from consideration.						
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>5-8</u> is/are rejected.						
7) Claim(s) is/are objected to.	· · · · · · · · · · · · · · · · · · ·					
8) Claim(s) are subject to restriction and/or	election requirement.					
Application Papers						
9) The specification is objected to by the Examine	r.					
10) The drawing(s) filed on is/are: a) accepted or b) objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).						
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. § 119						
12)⊠ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a)⊠ All b)□ Some * c)□ None of:						
1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No						
						3. Copies of the certified copies of the priority documents have been received in this National Stage
application from the International Bureau	ı (PCT Rule 17.2(a)).					
* See the attached detailed Office action for a list of the certified copies not received.						
Attachment(s)						
1) X Notice of References Cited (PTO-892)	4) Interview Summary					
<ul> <li>2) Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)</li> </ul>	Paper No(s)/Mail Da 5) Notice of Informal P	ate atent Application (PTO-152)				
Paper No(s)/Mail Date 7/11/2005.	6) Other:	,				

Application/Control Number: 10/809,011

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### **DETAILED ACTION**

This Office Action is in response to a Divisional filed on 3/25/2004.

Currently, claims 5-8 are pending.

## Specification

1. The specification has not been checked to the extent necessary to determine the presence of all possible minor errors. Applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

## Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 3. Claims 5-8 are rejected under 35 U.S.C. 102(e) as being anticipated by Akaishi et al. (U. S. Patent No. 6,255,154 filed 2/24/2000).

Akaishi shows the method as claimed, in Figs. 1-11B and corresponding text as: forming a body region (3) by implanting to diffuse an impurity in a predetermined region of a semiconductor layer (col. 3, lines 5-15); after field-oxidizing a surface region of said semiconductor layer by way of the LOCOS method to form an insulating film, forming a first insulating film (9) by patterning said insulating film while a resist film formed on a predetermined region of said insulating film is employed as a mask (col. 3, lines 26-51);

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forming a second gate insulating film (30) on said semiconductor layer other than said first gate insulating film (col. 4, lines 10-22), and then forming a gate electrode (7A) so that said gate electrode is bridged over said first gate insulating film and said second gate insulating film (col. 5, lines 39-56); and forming a source region and drain region by implanting an impurity of an opposite conductive type to said body region into both a source forming region formed within said body region and a drain forming region formed within said semiconductor layer while a resist film (34) having an opening is employed as a mask (col. 4, lines 35-54) (claim 5). Akaishi teaches that the device separation film (9) is formed in the same step of forming said first gate insulating film (col. 3, lines 16-25) (claim 6). Akaishi teaches that the first gate insulating film is not formed at a position lower than at least a surface position of said semiconductor layer in the step of forming said first gate insulating film (col. 3, lines 16-25) (claim 7). Akaishi teaches that in the step of forming the first gate insulating film, said first gate insulating film is not formed at a position lower than a surface position of said semiconductor layer so that local current crowding is not produced between at least an edge portion of said body region and an edge portion of said first gate insulating film (col. 3, line 57-col. 4, line 5) (claim 8).

### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Walter L. Lindsay, Jr. whose telephone number is (571) 272-1674. The examiner can normally be reached on Monday-Thursday.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael S. Lebentritt can be reached on (571) 272-1873. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

> Walter L. Lindsay, Jr. Examiner<sup>®</sup> Art Unit 2812

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